



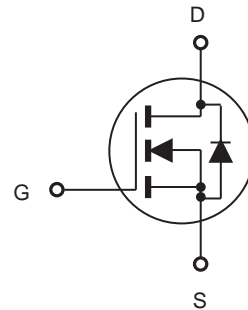
CEP160N08S/CEB160N08S

N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

- 80V, 152A, $R_{DS(ON)} = 3.6m$ @ $V_{GS} = 10V$
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- RoHS compliant.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous @ $T_C = 25^\circ C$ @ $T_C = 100^\circ C$	I_D	152	A
		107	A
Drain Current-Pulsed ^a	I_{DM}	608	A
Maximum Power Dissipation @ $T_C = 25^\circ C$ - Derate above $25^\circ C$	P_D	150	W
		1	W/ $^\circ C$
Single Pulsed Avalanche Energy ^d	E_{AS}	320	mJ
Single Pulsed Avalanche Current ^d	I_{AS}	40	A
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	R_{JC}	1	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	R_{JA}	62.5	$^\circ C/W$

This is preliminary information on a new product in development now .
Details are subject to change without notice .

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<http://www.cetsemi.com>

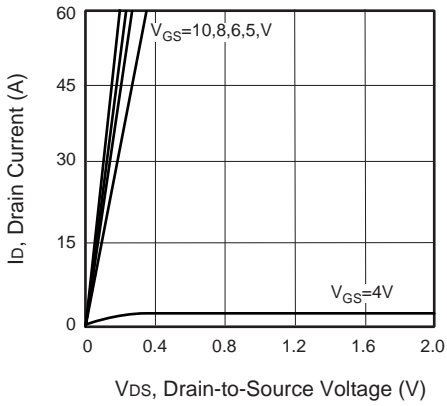


Figure 1. Output Characteristics

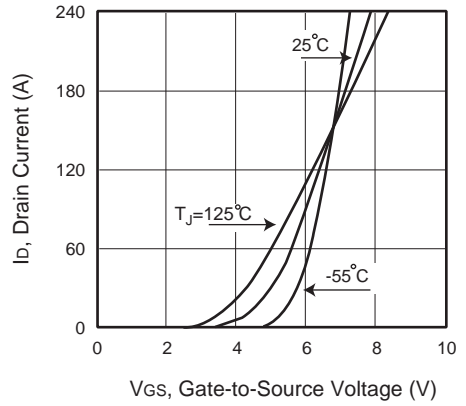


Figure 2. Transfer Characteristics

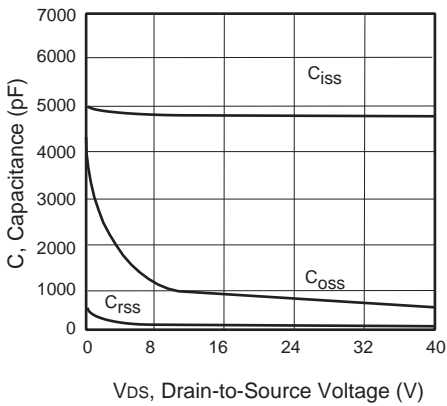


Figure 3. Capacitance

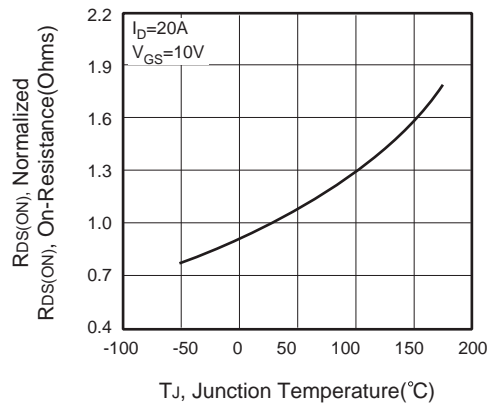


Figure 4. On-Resistance Variation with Temperature

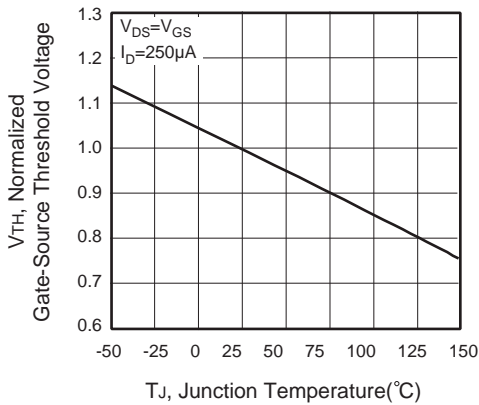


Figure 5. Gate Threshold Variation with Temperature

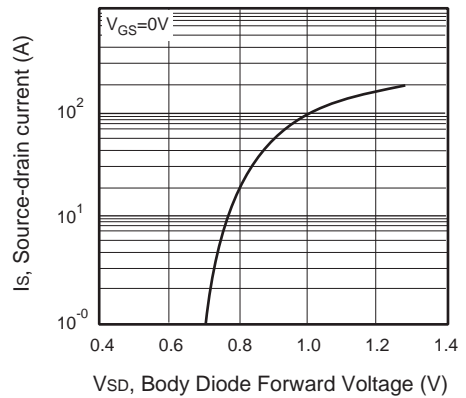


Figure 6. Body Diode Forward Voltage Variation with Source Current

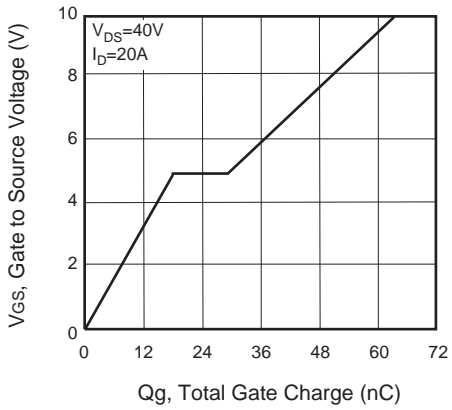


Figure 7. Gate Charge

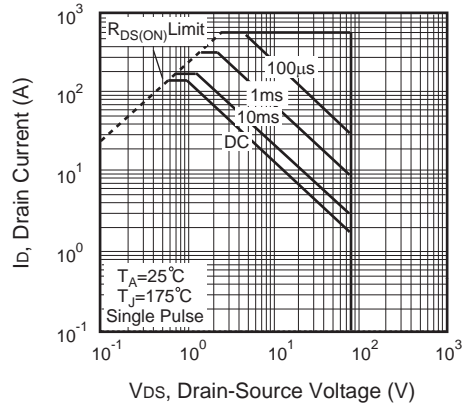


Figure 8. Maximum Safe Operating Area

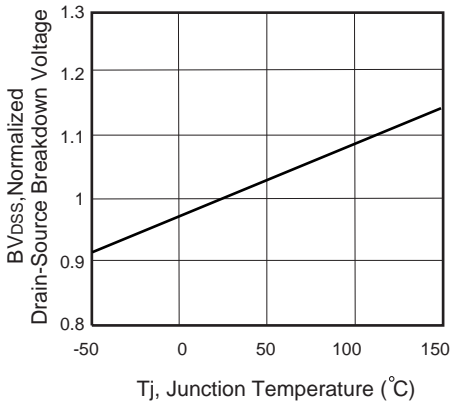


Figure 9. Breakdown Voltage Variation VS Temperature

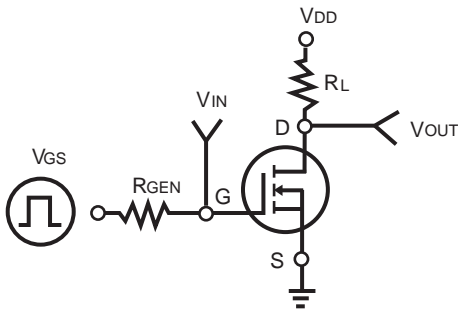


Figure 10. Switching Test Circuit

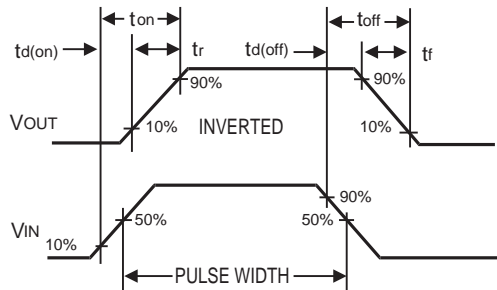


Figure 11. Switching Waveforms

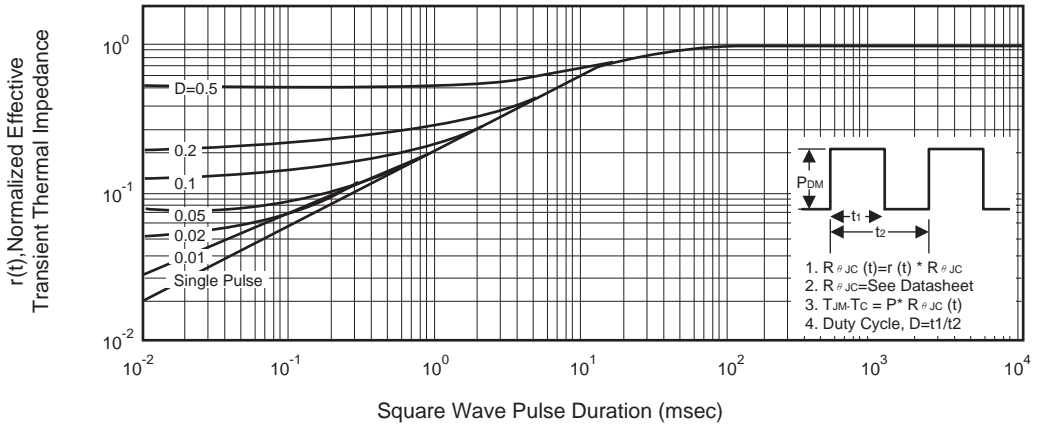


Figure 12. Normalized Thermal Transient Impedance Curve